

### SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

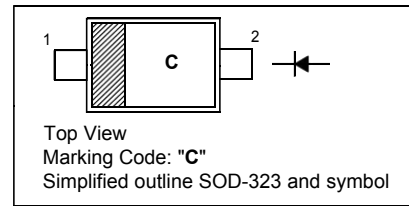
for low current rectification and high speed switching applications

**Features**

- Extremely small surface mounting type

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



**Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)**

Parameter	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	30	V
Mean Rectifying Current	I <sub>O</sub>	200	mA
Peak Forward Surge Current (60Hz for Cyc.)	I <sub>FSM</sub>	1	A
Junction Temperature	T <sub>j</sub>	125	°C
Storage Temperature Range	T <sub>stg</sub>	- 40 to + 125	°C

**Characteristics at T<sub>a</sub> = 25 °C**

Parameter	Symbol	Max.	Unit
Forward Voltage at I <sub>F</sub> = 200 mA	V <sub>F</sub>	0.6	V
Reverse Current at V <sub>R</sub> = 10 V	I <sub>R</sub>	30	μA



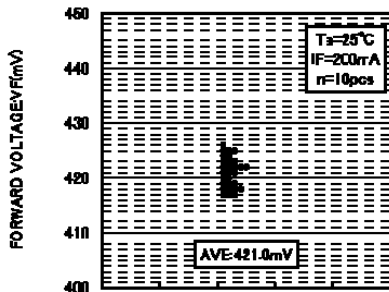
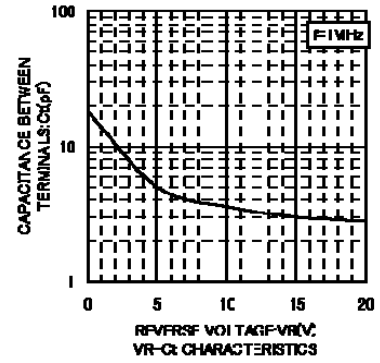
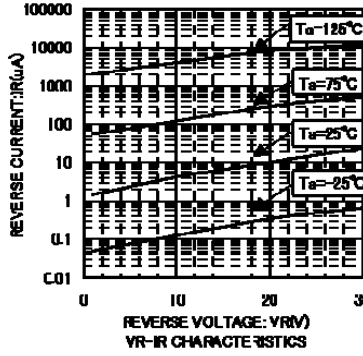
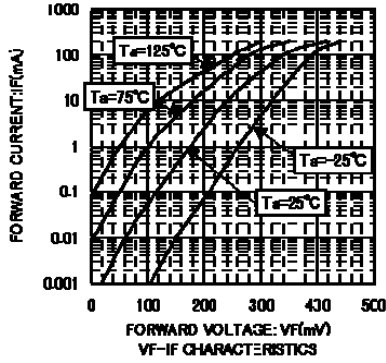
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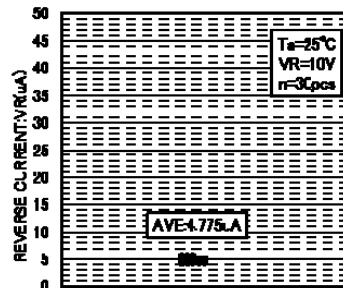
RB521V\_30



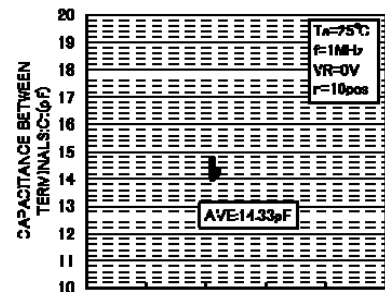
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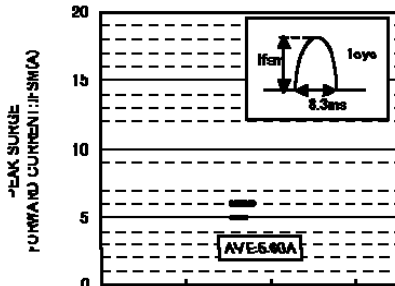
VF DISPERSION MAP



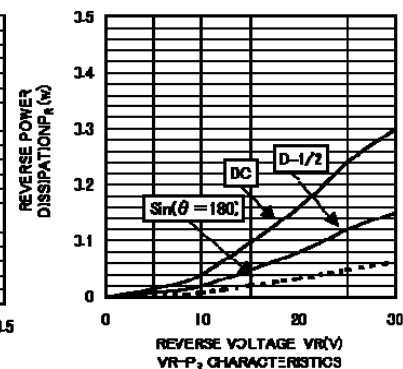
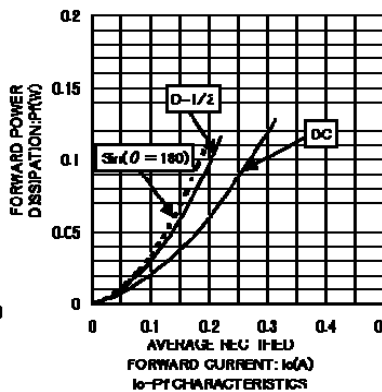
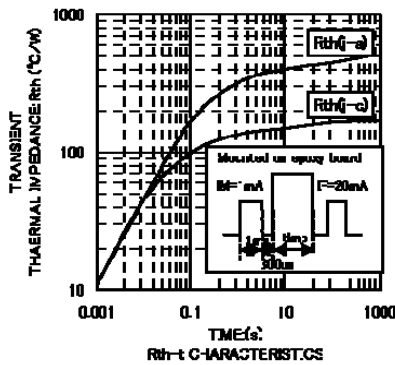
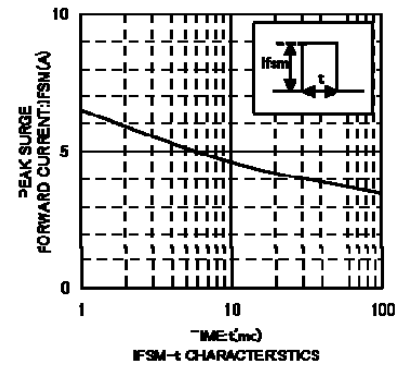
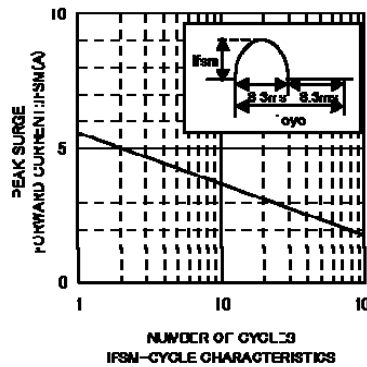
IR DISPERSION MAP



Ct DISPERSION MAP



FSM DISPERSION MAP

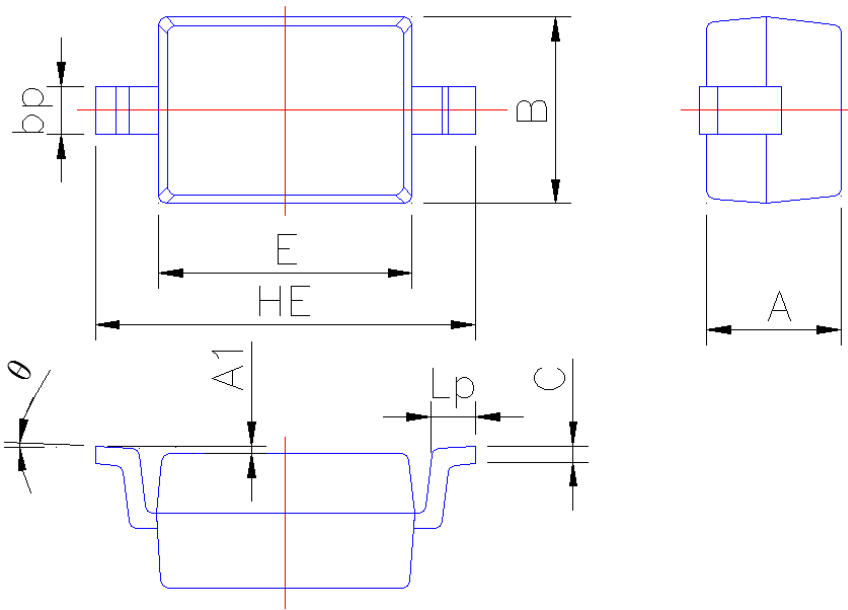




## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°